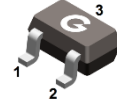
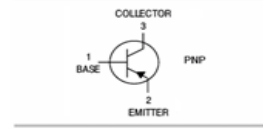


Features

- Epitaxial planar die construction
- Complement to MMST4401

HF



SOT-323

Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMST4403	SOT-323	3000 pcs / Tape & Reel	K3T

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Breakdown Voltage	V _{CEO}	-40	V
Emitter-Base Breakdown Voltage	V _{EBO}	-5	V
Collector Current (Continuous)	I _C	-0.6	A
Collector Current (Peak)	I _{CM}	-1.2	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation *1	P _D	0.2	W
Thermal Resistance Junction-to-Air *1	R _{θJA}	625	°C/W
Thermal Resistance Junction-to-Air *2	R _{θJA}	252	°C/W
Thermal Resistance Junction-to-Case *2	R _{θJC}	147	°C/W
Thermal Resistance Junction-to-Lead *2	R _{θJL}	174	°C/W
Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Notes:

1. Device mounted on a minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
2. The data tested by surface mounted on a 25.4mm * 25.4mm * 1mm FR4-epoxy P.C.B

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}$, $I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35\text{V}$, $I_E = 0$	-	-	-0.1	μA
Collector Cut-off Current	I_{CEX}	$V_{CE} = -35\text{V}$, $V_{EB(OFF)} = -0.4\text{V}$	-	-	-0.10	μA
Base Cut-off Current	I_{BL}	$V_{CE} = -35\text{V}$, $V_{EB(OFF)} = -0.4\text{V}$	-	-	-0.10	μA
DC Current Gain	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -0.1\text{mA}$	30	-	-	-
		$V_{CE} = -1\text{V}$, $I_C = -1\text{mA}$	60	-	-	-
		$V_{CE} = -1\text{V}$, $I_C = -10\text{mA}$	100	-	-	-
		$V_{CE} = -2\text{V}$, $I_C = -150\text{mA}$	100	-	300	-
		$V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$	20	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$	-	-	-0.4	V
		$I_C = -500\text{mA}$, $I_B = -50\text{mA}$	-	-	-0.75	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$	-0.75	-	-0.95	V
		$I_C = -500\text{mA}$, $I_B = -50\text{mA}$	-	-	-1.30	V
Current-Gain—Bandwidth Product	f_T	$V_{CE} = -10\text{V}$, $I_C = -20\text{mA}$ $f = 100\text{MHz}$	200	-	-	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	-	-	8.5	pF
Delay time	t_d	$V_{CC} = -30\text{V}$, $V_{BE(off)} = -2\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$	-	-	15	nS
Rise time	t_r		-	-	20	nS
Storage time	t_s	$V_{CC} = -30\text{V}$, $I_C = -150\text{mA}$	-	-	225	nS
Fall time	t_f	$I_{B1} = I_{B2} = -15\text{mA}$	-	-	30	nS

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

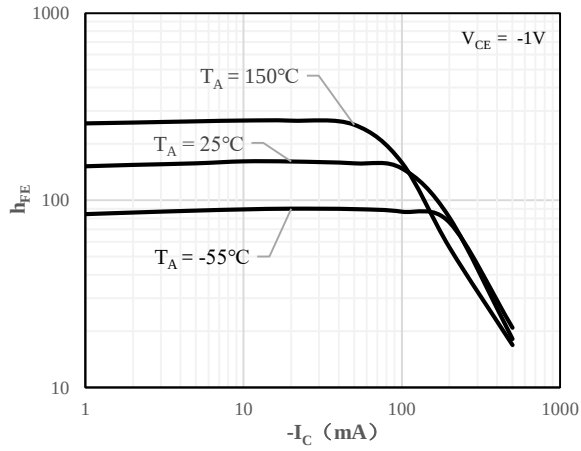


Fig 1 h_{FE} vs. I_C

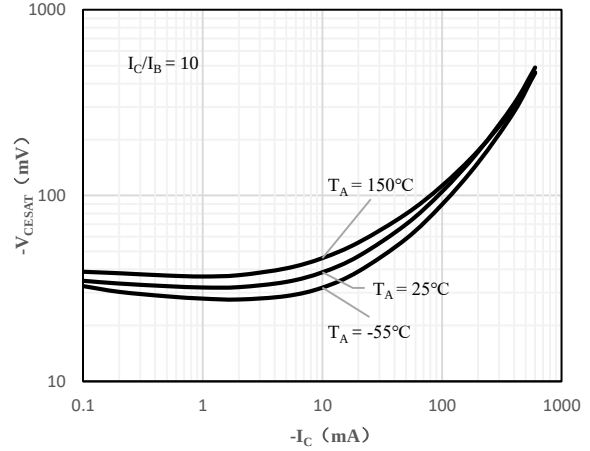


Fig 2 $V_{CE(sat)}$ vs. I_C

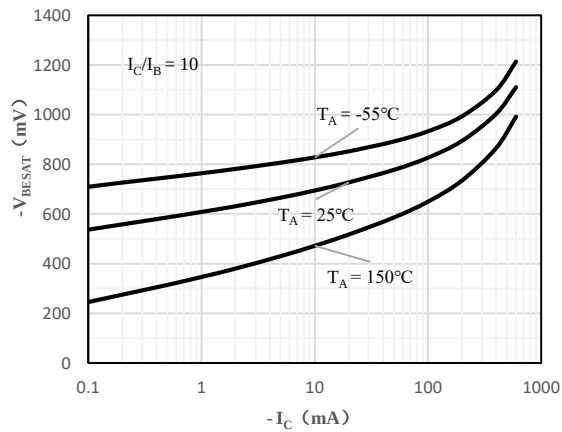


Fig 3 $V_{BE(sat)}$ vs. I_C

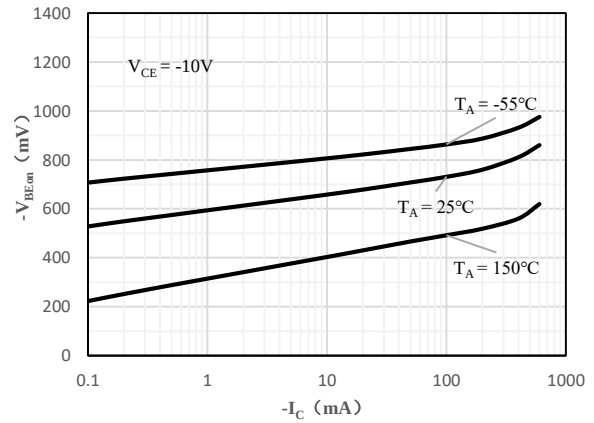
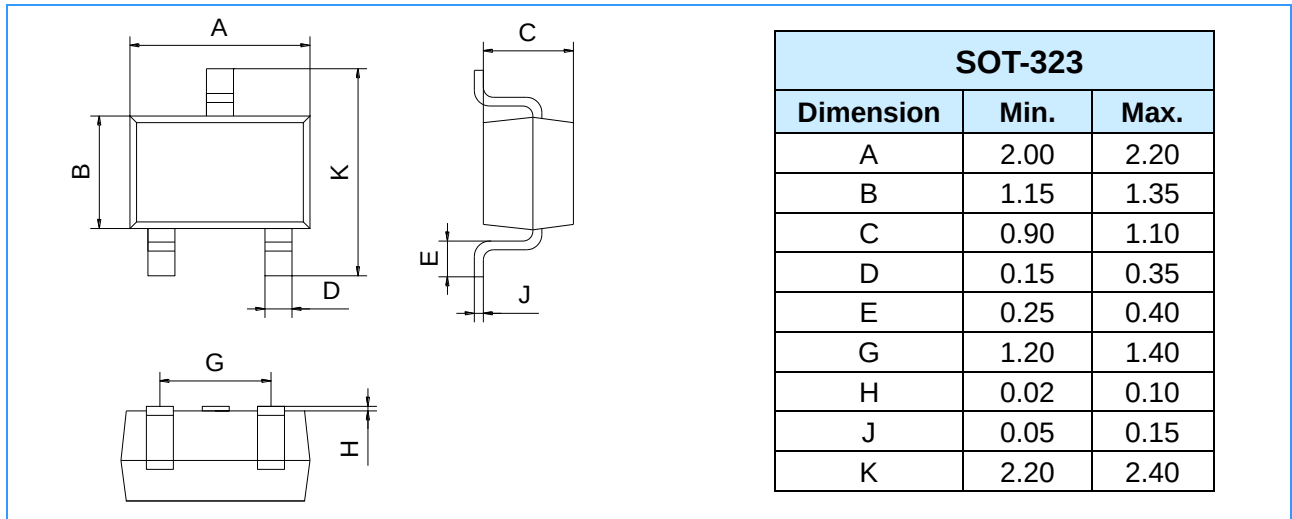
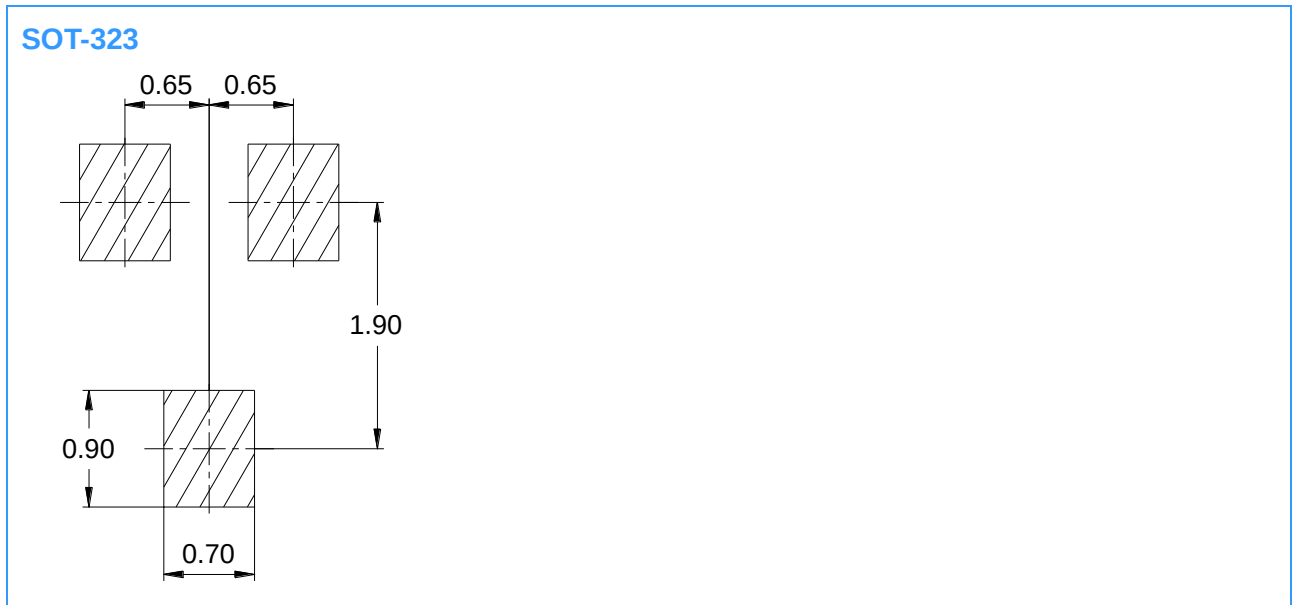


Fig 4 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Package Outline Dimensions (Unit: mm)



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